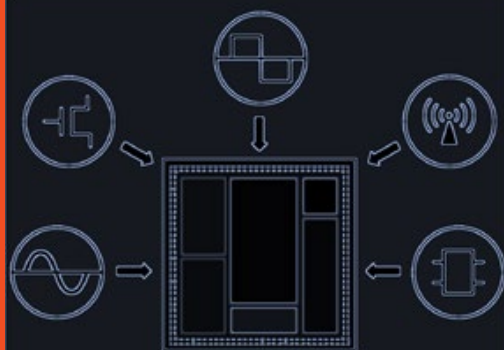




GLOBALFOUNDRIES®



130G/LP/EE

130 nm Process Technologies

Highlights

- 130G/LP Baseline Technology
 - + Manufactured in 300 mm facility in Singapore
 - + Volume production serving Mobile Cellular, Consumer and Digital/RF SoC
- 130EEPROM
 - + Extension of 130LP platform
 - + Leading EEPROM solution in the market
 - + Suitable for NFC, Smart Card, Consumer IC and MCU
- 110TS
 - + Cost optimized solution based on 130G platform
 - + For Bluetooth/RF SoC
- Comprehensive design ecosystem and services
 - + Full range of foundation and complex IP libraries
 - + eNVM IP including eFuse and OTP
- Extensive services and supply chain support
 - + Regularly scheduled MPWs
 - + Layout database consolidation and mask assembly services
 - + Industry-standard packaging and test solutions

The Right Technology for the Right Application™

GLOBALFOUNDRIES 130 nm process technology platform is most suited for general purpose SoC designs and power- and price-sensitive applications.

The comprehensive, highly-configurable and production-proven 130 nm platform solution enables integration of logic, RF, analog and non-volatile memory to provide a cost effective solution. GF is also the first foundry to offer a 130 nm EEPROM solution. Further die cost reduction is made possible with the 110TS platform, which is shipping in volume production.

		EEPROM
Analog + RF	Analog + RF	Analog + RF
1.2 V 2.5 or 3.3 V	1.2 V 3.3 V	1.5 V 3.3 V
130G	110TS/G	130LP
130 nm process technology platform		

Target Applications and Solutions

- Bluetooth SoC (110TS)
- Cellular (GSM/EDGE, TD-SCDMA) Radio (130LP)
- WiFi Radio (130G, 130LP)
- Active RFID (130G, 130LP/EE)
- Mobile TV Tuner (130G, 130LP)
- Smart card / Bank card (130LP/EE)
- MEMS ASIC (130G, 130LP)
- Drones (130LP)

Technology Overview

- 130LP: 1.5 V (Core) and 3.3 V (I/O) solutions
 - + 2 core device Vt's
 - + Mixed-signal, high voltage, RF plug-in modules
- 130G: 1.2 V (Core) and 2.5/3.3 V (I/O) solutions
 - + 3 core device Vt's
 - + Mixed-signal, RF plug-in modules
- 110TS: 1.2 V (Core) and 3.3 V (I/O)
 - + Shrink from 130G
 - + Comparable performance to 130G
- EEPROM Module (130LP): High endurance, low power
- Twin retrograde wells on P-substrate
- MIM capacitor, eFuse fuse/macro
- High quality passives, diodes and inductors
- Standard temperature range: -40°C to 125°C

IP Overview

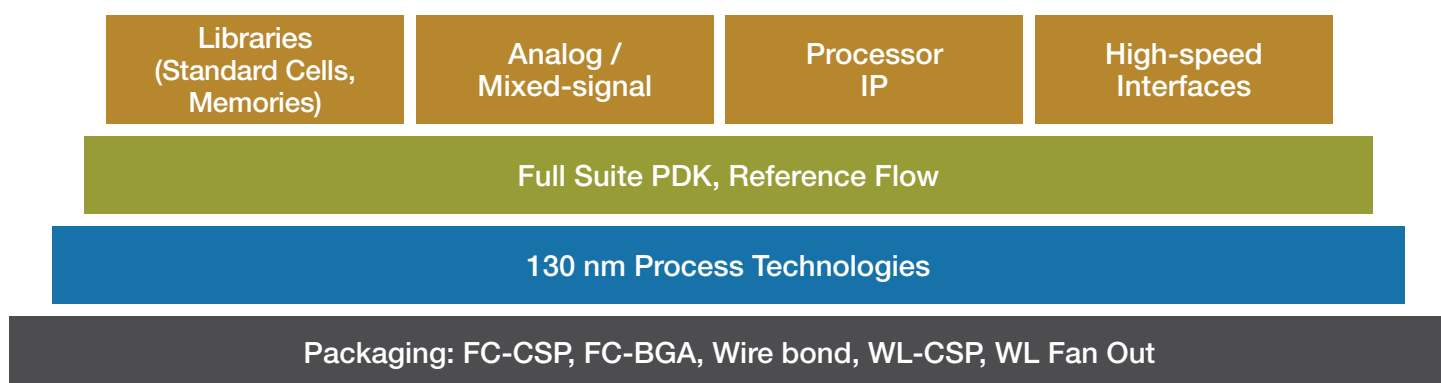
The comprehensive 130 nm Platform IP portfolio includes a wide range of silicon-proven high performance, power-optimized solutions for a broad set of applications.

Foundation IP		
Standard cell 1.5 V & 1.2 V (130LP)	Standard cell 1.2 V (130G)	GPIO
Memory		
High density memories	High speed memories (130LP)	
SRAM compiler	ROM Compiler	
Electrical Fuse macro	OTP macro	EEPROM
Analog IP		
DC-DC, PLL	Video DAC	Audio ADC/DAC
Interface IP		
SPIO (PCI)	USB 2.0 OTG/PHY	DDR DLL

Note: IP options vary by process selection.
Contact GF for IP availability.

GLOBALSOLUTIONS® Design and Manufacturing Ecosystem

GLOBALSOLUTIONS is the sum of our internal resources and ecosystem partners, combined to efficiently enable the fastest time-to-volume. This ecosystem includes partners in all aspects of design enablement and turnkey services, OPC and mask operations, and advanced capabilities in assembly solutions.



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